

Supplementary Information

Polymer Field-Effect Transistor Memory Based on Ferroelectric Nylon Gate Insulator

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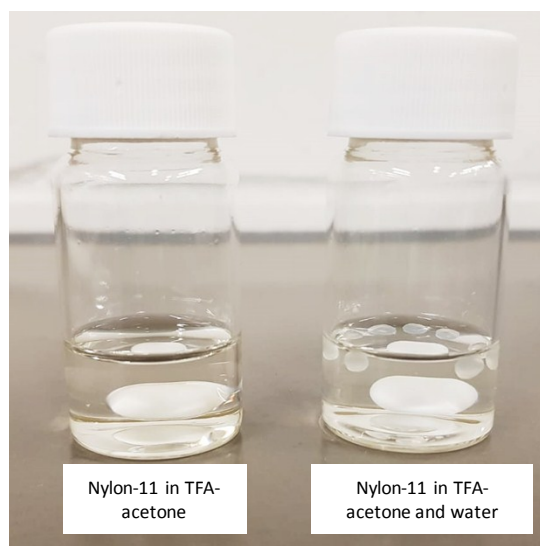


Figure S1. Photograph of nylon-11 in TFA:acetone (left) and TFA:acetone/water (50/50 mol %) mixture (right) after 1 hour of stirring at room temperature. Nylon-11 pellets completely dissolved in TFA:acetone, whereas, the pellets remained undissolved in TFA:acetone and water mixture.